

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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# 2SK1307

Silicon N-Channel MOS FET

**RENESAS**

ADE-208-1265 (Z)  
1st. Edition  
Mar. 2001

## Application

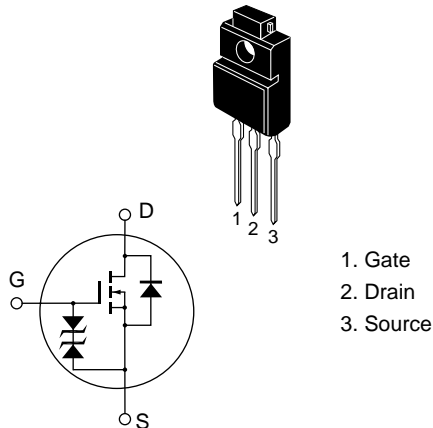
High speed power switching

## Features

- Low on-resistance
- High speed switching
- 4 V gate drive device
  - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

## Outline

TO-220FM



## Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	100	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	20	A
Drain peak current	I <sub>D(pulse)</sub> *1	80	A
Body to drain diode reverse drain current	I <sub>DR</sub>	20	A
Channel dissipation	Pch*2	35	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

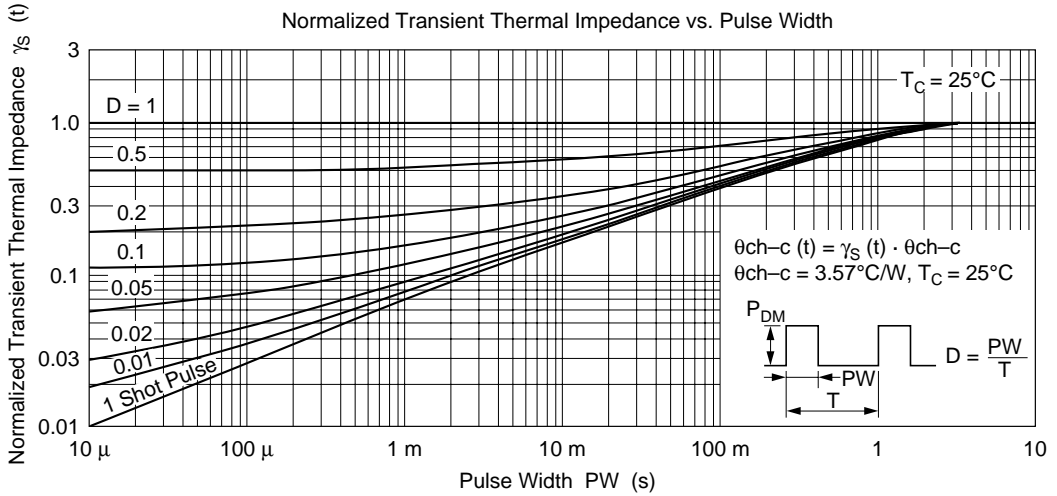
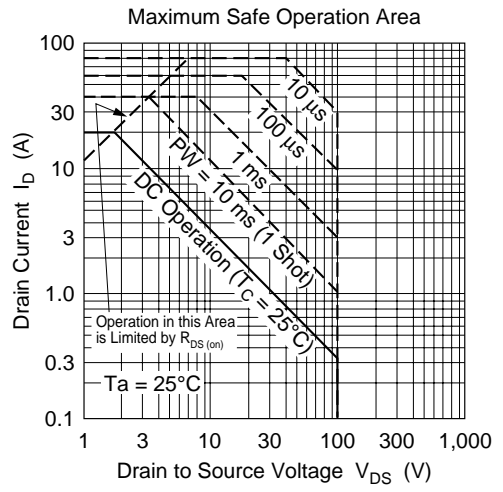
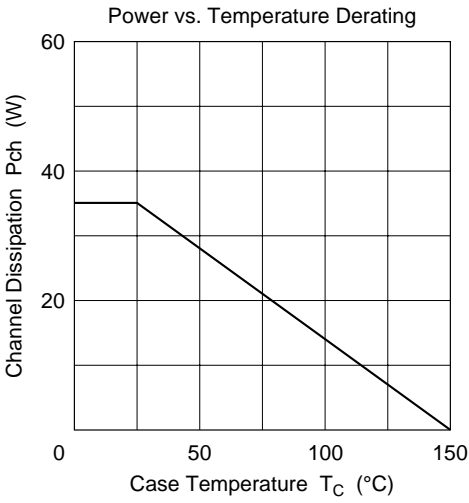
2. Value at T<sub>c</sub> = 25°C

## Electrical Characteristics (Ta = 25°C)

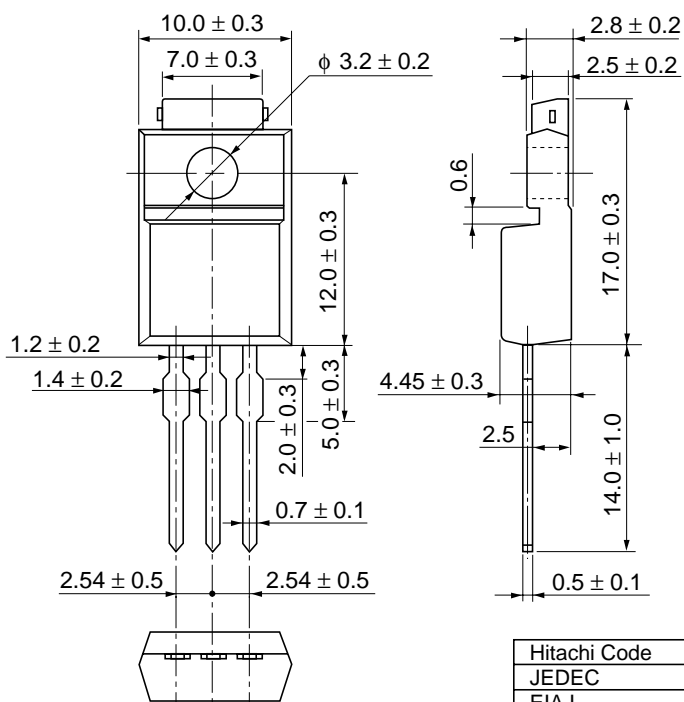
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 20$	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	250	$\mu\text{A}$	$V_{DS} = 80 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.065	0.085	$\Omega$	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
		—	0.085	0.12	$\Omega$	$I_D = 10 \text{ A}, V_{GS} = 4 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	10	16	—	S	$I_D = 10 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	$C_{iss}$	—	1300	—	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	$C_{oss}$	—	540	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	$C_{rss}$	—	160	—	pF	
Turn-on delay time	$t_{d(on)}$	—	12	—	ns	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	$t_r$	—	100	—	ns	$R_L = 3 \text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	—	300	—	ns	
Fall time	$t_f$	—	150	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	1.3	—	V	$I_F = 20 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	300	—	ns	$I_F = 20 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

See characteristic curves of 2SK1302.

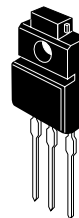


## Package Dimensions



As of January, 2001

Unit: mm



Hitachi Code	TO-220FM
JEDEC	—
EIAJ	Conforms
Mass (reference value)	1.8 g

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